OTTO VON GUERICKE UNIVERSITÄT MAGDEBURG

ABTEILUNG MATERIALPHYSIK

Veröffentlichungen

2024 | 2023 | 2022 | 2021 | 2020 | 2019 | 2018 | 2017 | 2016 | 2015 | 2014 | 2013 | 2012 | 2011 | 2010 | älter als 2010

() Liste der Publikationen der Abteilung Materialphysik seit 2010. Die meisten Publikationen sind direkt verlinkt. Wenn Sie Interesse an einer unserer Publikationen haben, sie aber nicht erhalten können, sprechen Sie uns bitte direkt an! ()

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- E. Baron, R. Goldhahn, S. Espinoza, M. Zahradik, M. Rebarz, J. Andreasson, M. Deppe. D.J. As, and M. Feneberg
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  Eur. J. Inorg. Chem. **26**, e202300027 (2023).

- E. Kluth, M.W. Fay, C. Parmenter, J.W. Roberts, E. Smith, C.T. Stoppiello, F.C.-P. Massabuau, R. Goldhahn, and M. Feneberg
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  Appl. Phys. Lett. **122**, 092101 (2023).

- K. Egbo, E. Luna, J. Lähnemann, G. Hoffmann, A. Trampert, J. Grümbel, E. Kluth, M. Feneberg, R. Goldhahn, and O. Bierwagen
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- S. Wang, P. Liebing, F. Engelhardt, L. Hilfert, S. Busse, R. Goldhahn, and F. T. Edelmann
  Synthesis and Complexation Study of New Aminoalkynylamidinate Ligands
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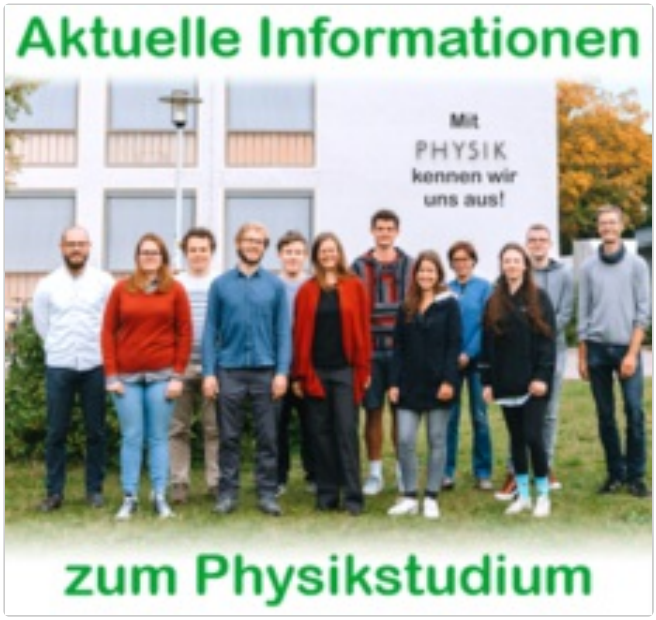
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